

TOSHIBA TRANSISTOR SILOCON NPN EPITAXIAL TYPE (PCT PROCESS)

# 2SC2120

AUDIO POWER AMPLIFIER APPLICATIONS

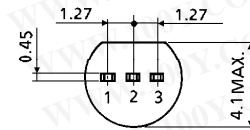
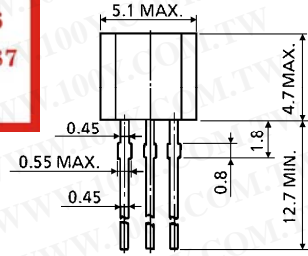
Unit in mm

- High  $h_{FE}$  :  $h_{FE}(1) = 100 \sim 320$
- 1 Watts Amplifier Applications.
- Complementary to 2SA950

勝特力材料 886-3-5753170  
 勝特力电子(上海) 86-21-54151736  
 勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	35	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	800	mA
Base Current	$I_B$	160	mA
Collector Power Dissipation	$P_C$	600	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	$-55 \sim 150$	$^\circ\text{C}$



1. EMITTER
2. COLLECTOR
3. BASE

JEDEC	TO-92
EIAJ	SC-43
TOSHIBA	2-5F1B

Weight : 0.21g

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 35\text{V}, I_E = 0$	—	—	0.1	$\mu\text{A}$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$	—	—	0.1	$\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}, I_B = 0$	30	—	—	V
DC Current Gain	$h_{FE}(1)$ (Note)	$V_{CE} = 1\text{V}, I_C = 100\text{mA}$	100	—	320	
	$h_{FE}(2)$	$V_{CE} = 1\text{V}, I_C = 700\text{mA}$	35	—	—	
Collector-Emitter Breakdown Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 20\text{mA}$	—	—	0.5	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = 1\text{V}, I_C = 10\text{mA}$	0.5	—	0.8	V
Transition Frequency	$f_T$	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	—	120	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0,$ $f = 1\text{MHz}$	—	13	—	pF

Note :  $h_{FE}(1)$  Classification    O : 100~200,    Y : 160~3200

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